G3R40MT12-CAL
1200 V 40 mΩ SiC MOSFET

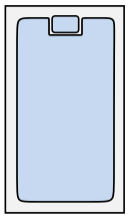
Silicon Carbide MOSFET
N-Channel Enhancement Mode

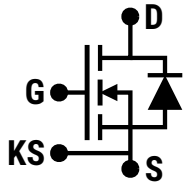
V_{DS}	=	1200 V
$R_{DS(ON)(Typ.)}$	=	40 mΩ
$I_{D(T_C = 100°C)}$	=	45 A

Features

- G3R™ Technology with +15 V Gate Drive
- Superior Q_G x $R_{DS(ON)}$ Figure of Merit
- Superior Cost-Performance Index
- Low Capacitances and Low Gate Charge
- Fast and Reliable Body Diode
- Low Losses at All Operating Temperatures

Bare Chip





D = Drain
G = Gate
S = Source
KS = Kelvin Source

Advantages

- Compatible with Commercial Gate Drivers
- Increased Power Density for Compact System
- High Frequency Switching
- Improved Thermal Capability
- Ease of Paralleing without Thermal Runaway

Applications

- Solar Inverters
- EV/HEV Charging
- Motor Drives
- High Voltage DC-DC Converters
- Switched Mode Power Supplies
- UPS
- Smart Grid Transmission and Distribution
- Induction Heating and Welding

Absolute Maximum Ratings (At T_C = 25°C Unless Otherwise Stated)

Parameter	Symbol	Conditions	Values	Unit	Note
Drain-Source Voltage	$V_{DS(max)}$	V_{GS} = 0 V, I_D = 100 µA	1200	V	
Gate-Source Voltage (Dynamic)	$V_{GS(max)}$		-10 / +20	V	
Gate-Source Voltage (Static)	$V_{GS(op)}$	Recommended Operation	-5 / +15	V	
Continuous Forward Current	I_D	T_C = 25°C, V_{GS} = -5 / +15 V T_C = 100°C, V_{GS} = -5 / +15 V T_C = 135°C, V_{GS} = -5 / +15 V	63 45 33	A	
Pulsed Drain Current	$I_{D(pulse)}$	t_P ≤ 3µs, D ≤ 1%, V_{GS} = 15 V, Note 1	150	A	
Power Dissipation	P_D	T_c = 25°C	297	W	Note 2
Non-Repetitive Avalanche Energy	E_{AS}	L = 2.4 mH, I_{AS} = 17.5 A	374	mJ	
Operating and Storage Temperature	T_j , T_{stg}		-55 to 175	°C	

Note 1: Pulse Width t_P Limited by $T_{j(max)}$

Note 2: Assuming $Rth_{JC(max)}$ = 0.5°C/W

Electrical Characteristics (At T_C = 25°C Unless Otherwise Stated)

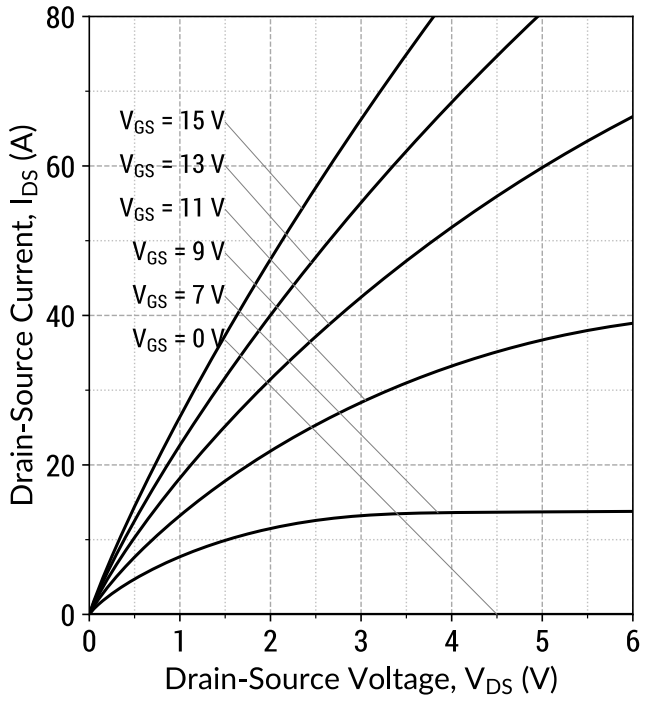
Parameter	Symbol	Conditions	Values			Unit	Note
			Min.	Typ.	Max.		
Drain-Source Breakdown Voltage	V_{DSS}	V_{GS} = 0 V, I_D = 100 µA	1200			V	
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS} = 1200 V, V_{GS} = 0 V		1		µA	
Gate Source Leakage Current	I_{GSS}	V_{DS} = 0 V, V_{GS} = 20 V V_{DS} = 0 V, V_{GS} = -10 V			100 -100	nA	
Gate Threshold Voltage	$V_{GS(th)}$	V_{DS} = V_{GS}, I_D = 18.0 mA V_{DS} = V_{GS}, I_D = 18.0 mA, T_j = 175°C	1.8	2.70 2.05		V	Fig. 9
Transconductance	g_{fs}	V_{DS} = 10 V, I_D = 35 A V_{DS} = 10 V, I_D = 35 A, T_j = 175°C		16.1 18.1		S	Fig. 4
Drain-Source On-State Resistance	$R_{DS(ON)}$	V_{GS} = 15 V, I_D = 35 A V_{GS} = 15 V, I_D = 35 A, T_j = 175°C		40 57	52	mΩ	Fig. 5-8
Input Capacitance	C_{iss}	V_{DS} = 800 V, V_{GS} = 0 V f = 1 MHz, V_{AC} = 25mV		2897		pF	Fig. 11
Output Capacitance	C_{oss}			88			
Reverse Transfer Capacitance	C_{rss}			7.1			
C_{oss} Stored Energy	E_{oss}			34		µJ	Fig. 12
C_{oss} Stored Charge	Q_{oss}			127		nC	
Gate-Source Charge	Q_{gs}	V_{DS} = 800 V, V_{GS} = -5 / +15 V I_D = 35 A Per IEC607478-4		29		nC	Fig. 10
Gate-Drain Charge	Q_{gd}			28			
Total Gate Charge	Q_g			88			
Internal Gate Resistance	$R_{G(int)}$	f = 1 MHz, V_{AC} = 25 mV		1.2		Ω	
Turn-On Switching Energy (Body Diode)	E_{On}	T_j = 25°C; V_{GS} = -5/+15V; $R_{G(ext)}$ = 8 Ω, I_D = 35 A; V_{DD} = 800 V		200		µJ	Fig. 18
Turn-Off Switching Energy (Body Diode)	E_{Off}			74			
Turn-On Delay Time	$t_{d(on)}$	V_{DD} = 800 V, V_{GS} = -5/+15V $R_{G(ext)}$ = 8 Ω, I_D = 35 A Timing relative to V_{DS}, Resistive load		19		ns	Fig. 20
Rise Time	t_r			22			
Turn-Off Delay Time	$t_{d(off)}$			17			
Fall Time	t_f			13			

Reverse Diode Characteristics

Parameter	Symbol	Conditions	Values			Unit	Note
			Min.	Typ.	Max.		
Diode Forward Voltage	V_{SD}	V_{GS} = -5 V, I_{SD} = 17 A V_{GS} = -5 V, I_{SD} = 17 A, T_j = 175°C		4.8 4.3		V	Fig. 13-14
Continuous Diode Forward Current	I_S	V_{GS} = -5 V, T_c = 100°C	27			A	
Diode Pulse Current	$I_{S(pulse)}$	V_{GS} = -5 V, Note 1		108		A	
Reverse Recovery Time	t_{rr}	V_{GS} = -5 V, I_{SD} = 35 A, V_R = 800 V dif/dt = 1000 A/µs, T_j = 25°C		19		ns	
Reverse Recovery Charge	Q_{rr}			120		nC	
Peak Reverse Recovery Current	I_{rrm}			5		A	
Reverse Recovery Time	t_{rr}	V_{GS} = -5 V, I_{SD} = 35 A, V_R = 800 V dif/dt = 1000 A/µs, T_j = 175°C		29		ns	
Reverse Recovery Charge	Q_{rr}			300		nC	
Peak Reverse Recovery Current	I_{rrm}			9		A	

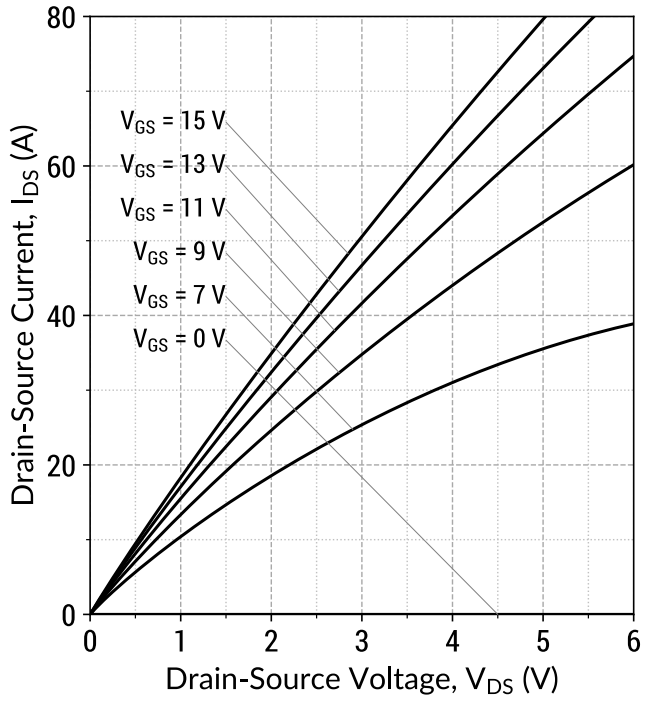
**The chip technology was characterized up to 200 V/ns. The measured dV/dt was limited by measurement test setup and package.*

Figure 1: Output Characteristics (T_j = 25°C)



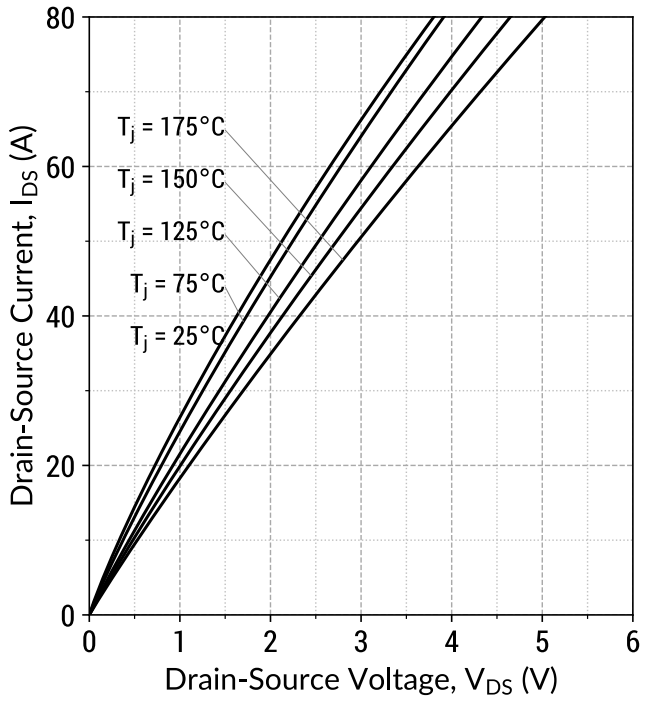
$I_D = f(V_{DS}, V_{GS})$; t_P = 250 µs

Figure 2: Output Characteristics (T_j = 175°C)



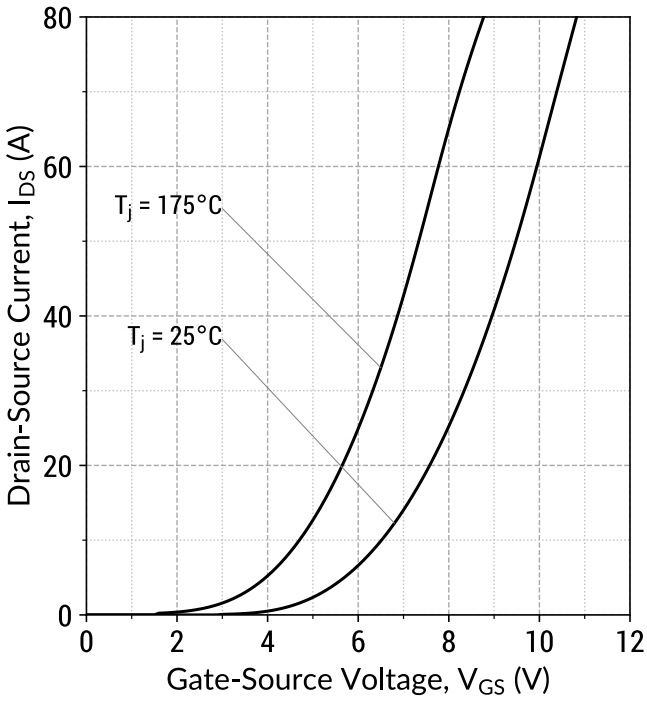
$I_D = f(V_{DS}, V_{GS})$; t_P = 250 µs

Figure 3: Output Characteristics (V_{GS} = 15 V)



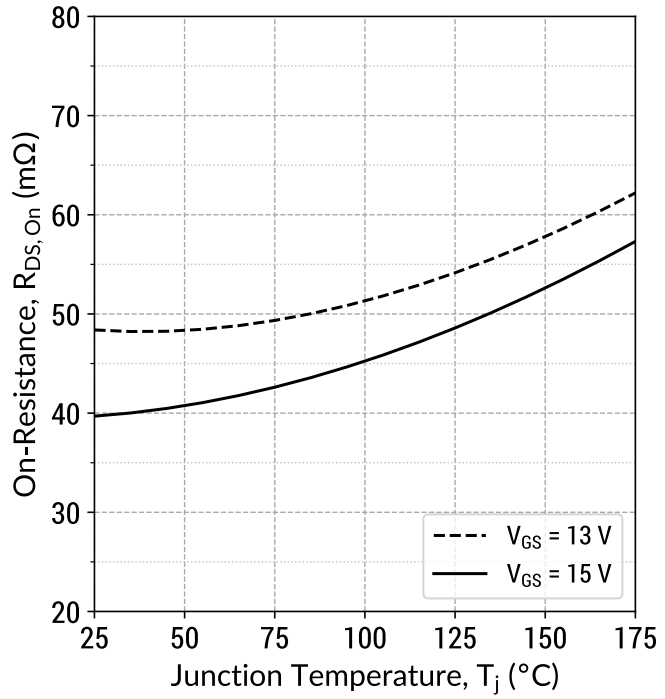
$I_D = f(V_{DS}, T_j)$; t_P = 250 µs

Figure 4: Transfer Characteristics (V_{DS} = 10 V)



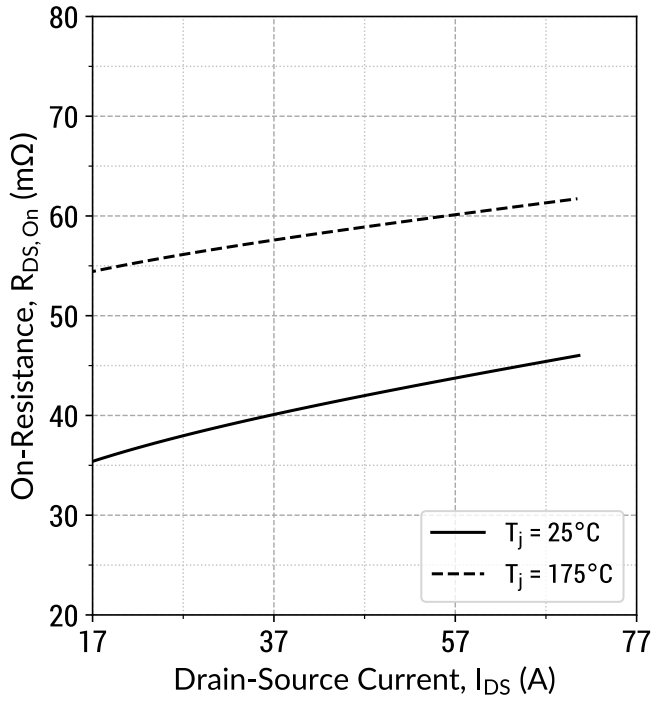
$I_D = f(V_{GS}, T_j)$; t_P = 100 µs

Figure 5: On-State Resistance v/s Temperature



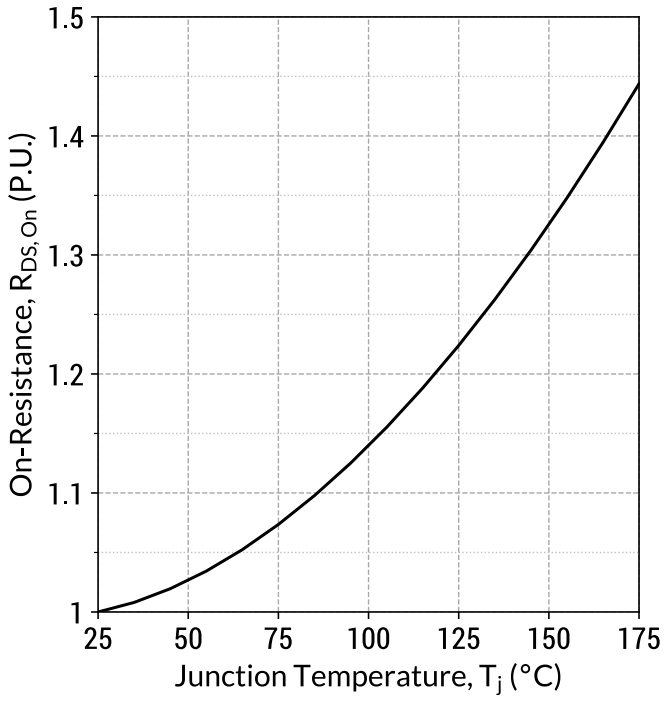
$R_{DS(ON)} = f(T_j, V_{GS})$; t_P = 250 µs; I_D = 35 A

Figure 6: On-State Resistance v/s Drain Current



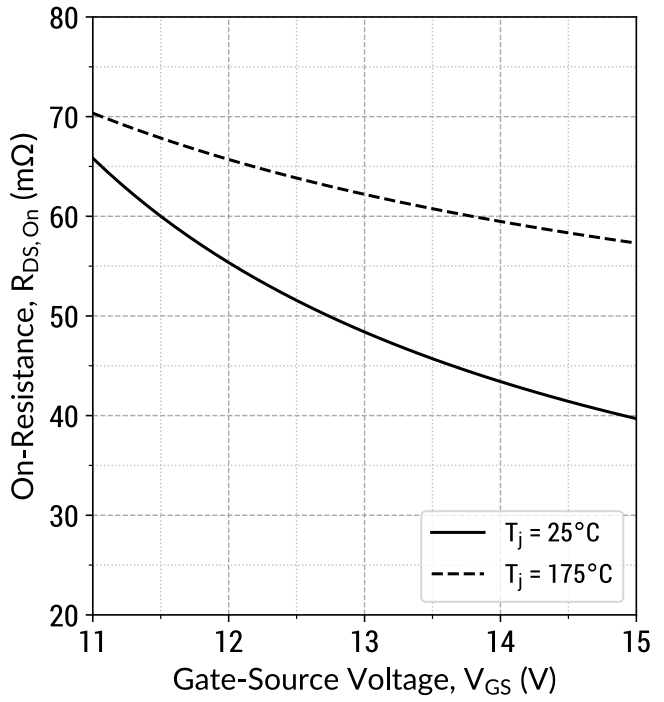
$R_{DS(ON)} = f(T_j, I_D)$; t_P = 250 µs; V_{GS} = 15 V

Figure 7: Normalized On-State Resistance v/s Temperature



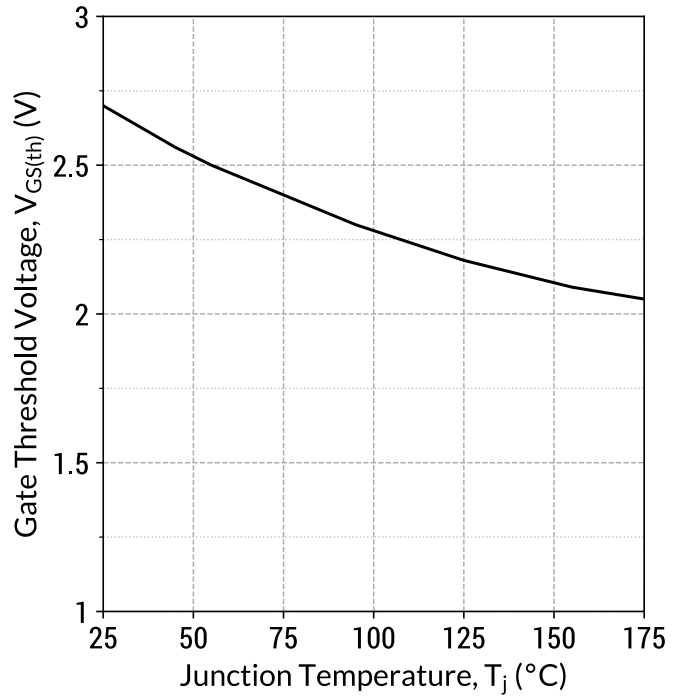
$R_{DS(ON)} = f(T_j)$; t_P = 250 µs; I_D = 35 A; V_{GS} = 15 V

Figure 8: On-State Resistance v/s Gate Voltage



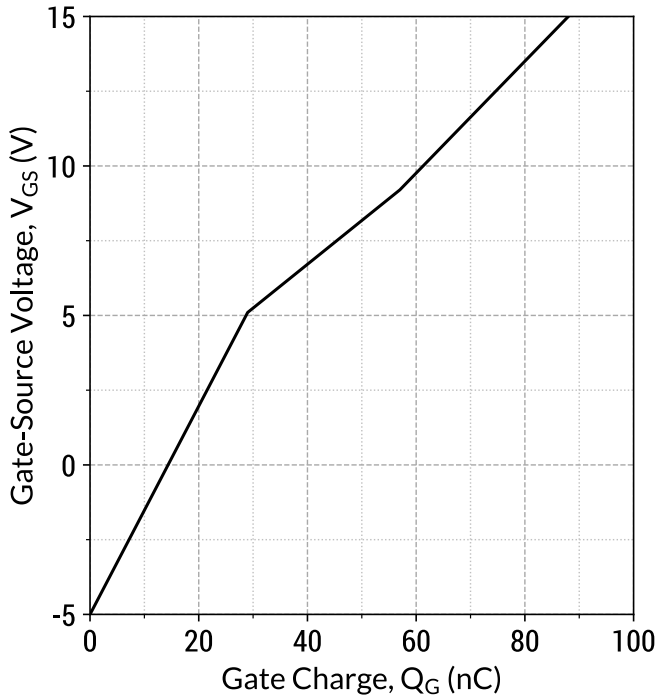
$R_{DS(ON)} = f(T_j, V_{GS})$; t_P = 250 µs; I_D = 35 A

Figure 9: Threshold Voltage Characteristics



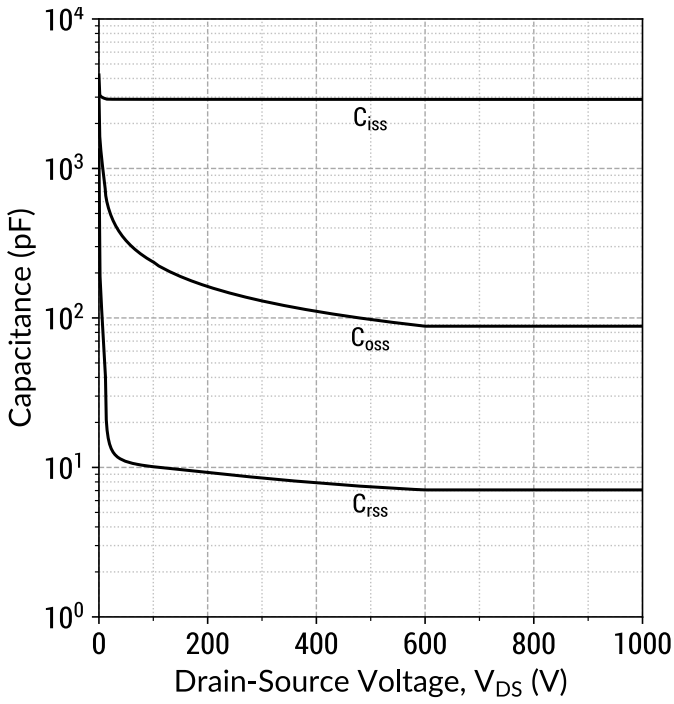
$V_{GS(th)} = f(T_j)$; $V_{DS} = V_{GS}$; I_D = 18.0 mA

Figure 10: Gate Charge Characteristics



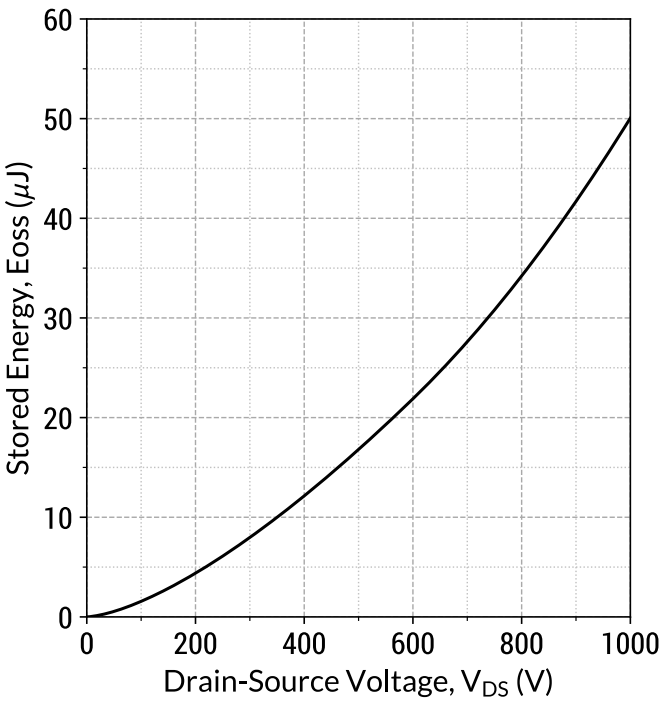
I_D = 35 A; V_{DS} = 800 V; T_c = 25°C

Figure 11: Capacitance v/s Drain-Source Voltage



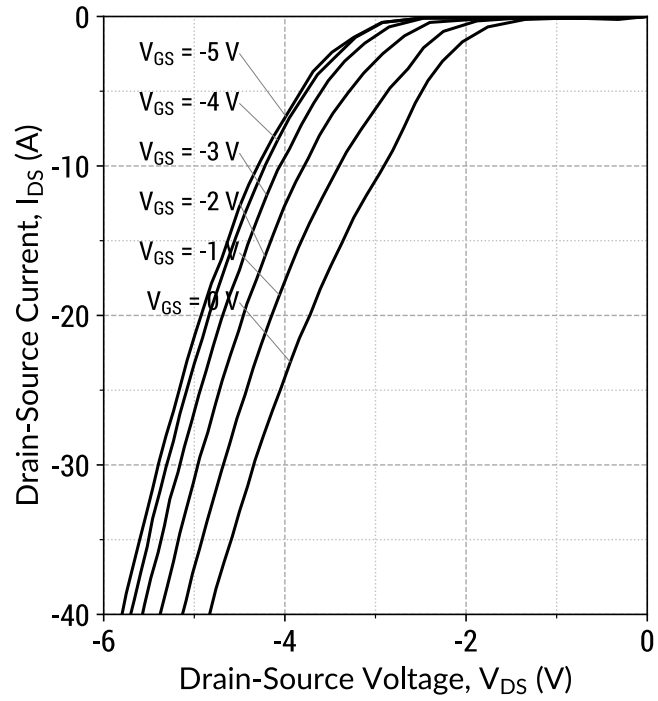
f = 1 MHz; V_{AC} = 25mV

Figure 12: Output Capacitor Stored Energy



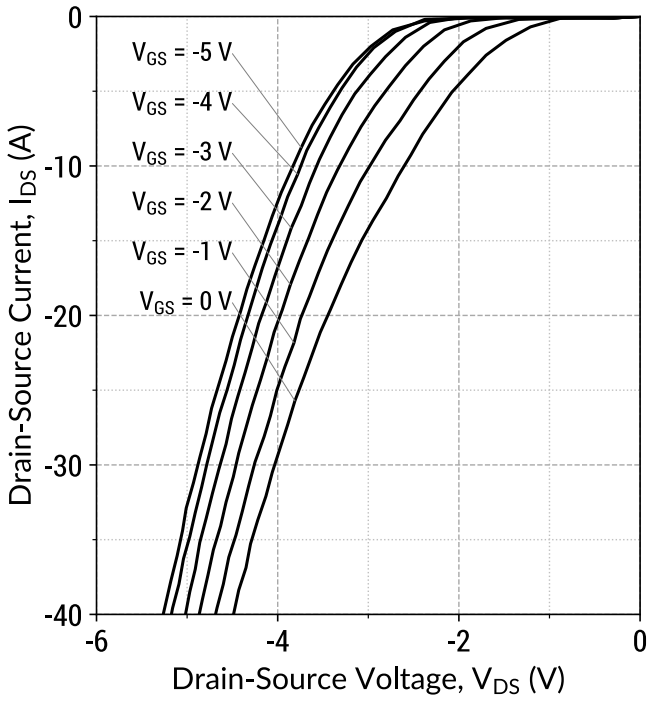
$E_{oss} = f(V_{DS})$

Figure 13: Body Diode Characteristics (T_j = 25°C)



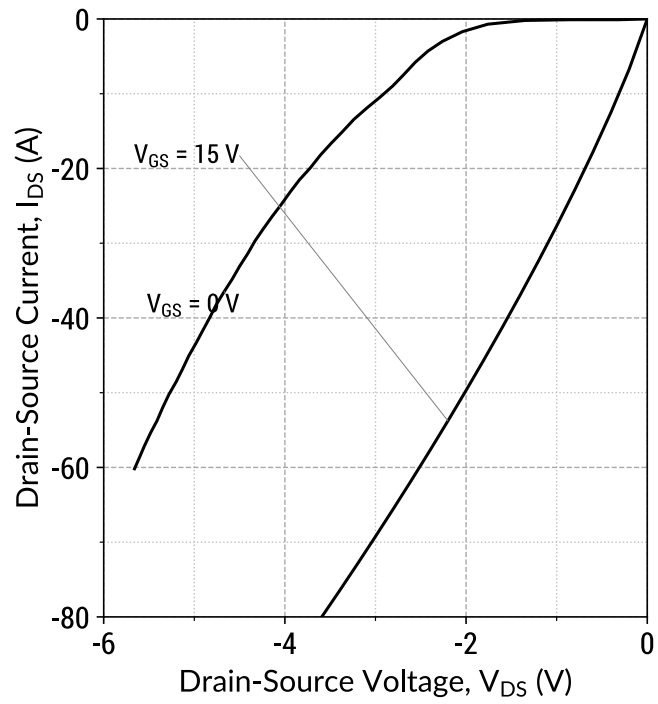
$I_D = f(V_{DS}, V_{GS})$; t_P = 250 µs

Figure 14: Body Diode Characteristics (T_j = 175°C)



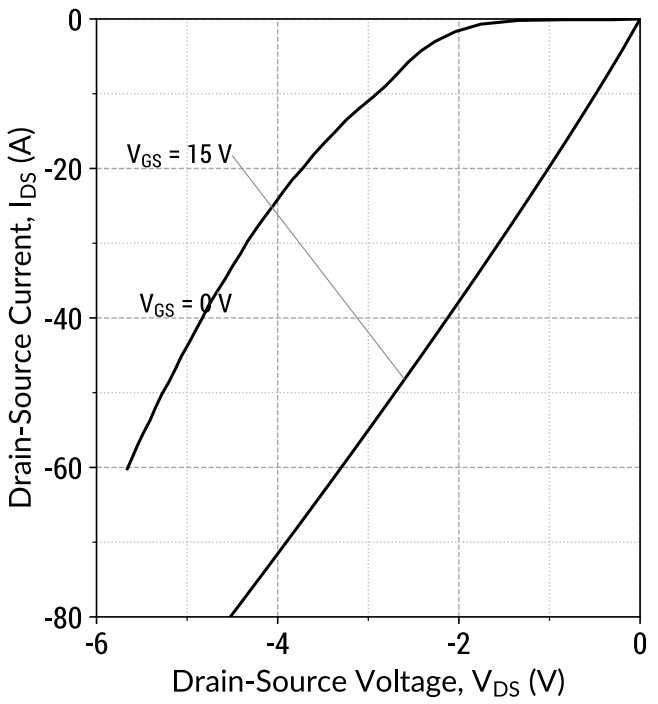
$I_D = f(V_{DS}, V_{GS})$; t_P = 250 µs

Figure 15: Third Quadrant Characteristics (T_j = 25°C)



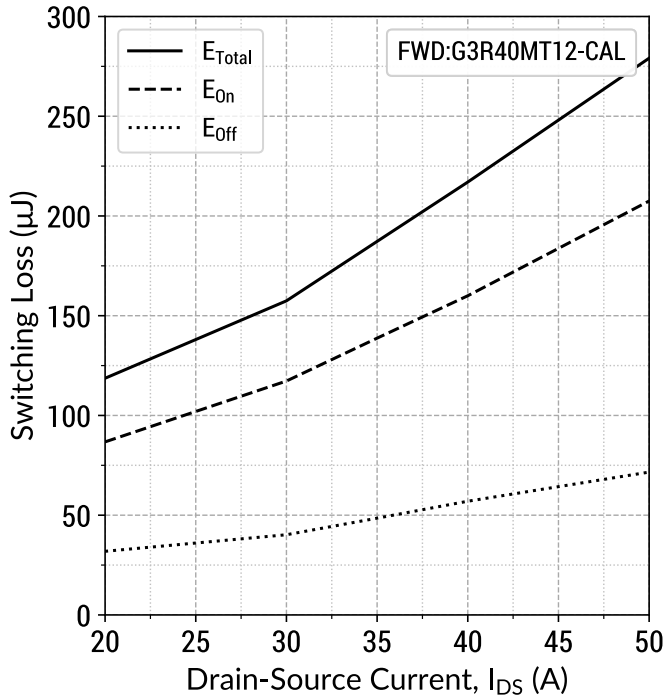
$I_D = f(V_{DS}, V_{GS})$; t_P = 250 µs

Figure 16: Third Quadrant Characteristics (T_j = 175°C)



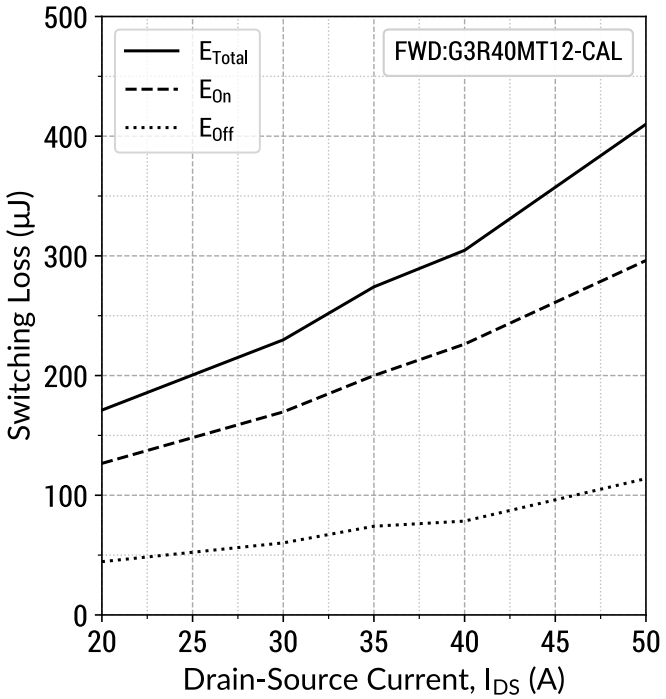
$I_D = f(V_{DS}, V_{GS})$; t_P = 250 µs

Figure 17: Resistive Switching Energy v/s Drain Current (V_{DD} = 600V)



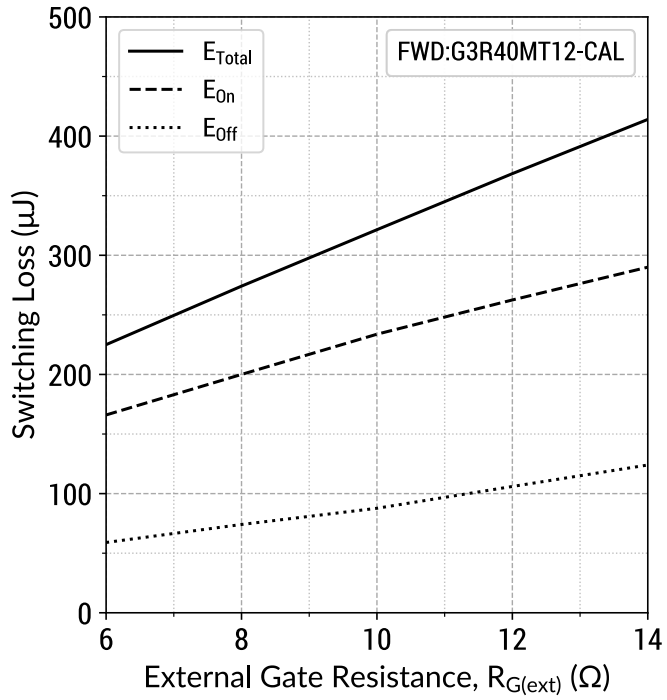
T_j = 25°C; V_{GS} = -5/+15V; $R_{G(ext)}$ = 8 Ω

Figure 18: Resistive Switching Energy v/s Drain Current (V_{DD} = 800V)



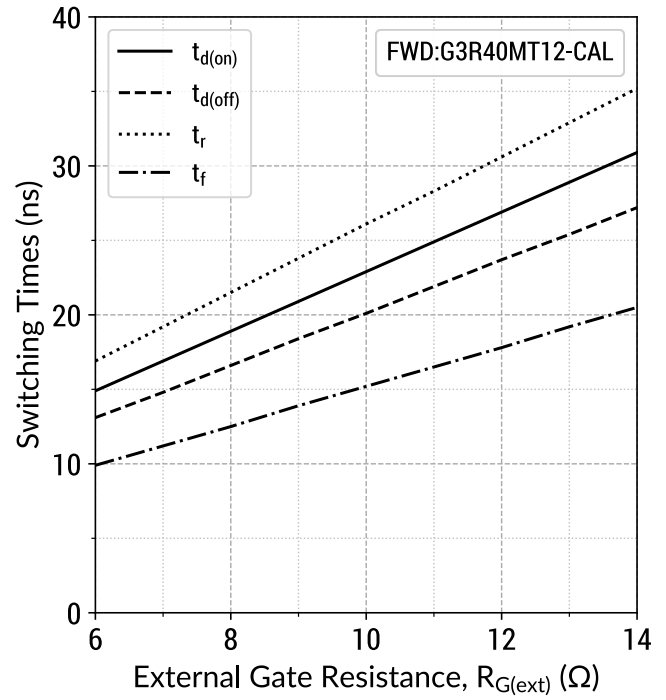
T_j = 25°C; V_{GS} = -5/+15V; $R_{G(ext)}$ = 8 Ω

Figure 19: Resistive Switching Energy v/s $R_{G(ext)}$ (V_{DD} = 800V)



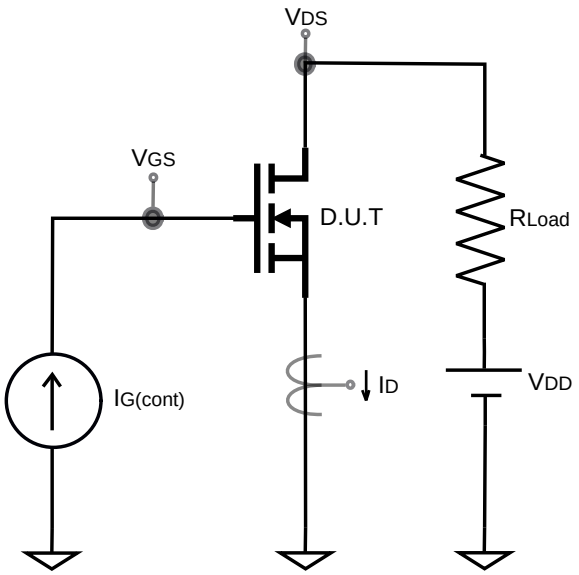
T_j = 25°C; V_{GS} = -5/+15V; I_{DS} = 35 A

Figure 20: Switching Time v/s $R_{G(ext)}$ (V_{DD} = 800V)

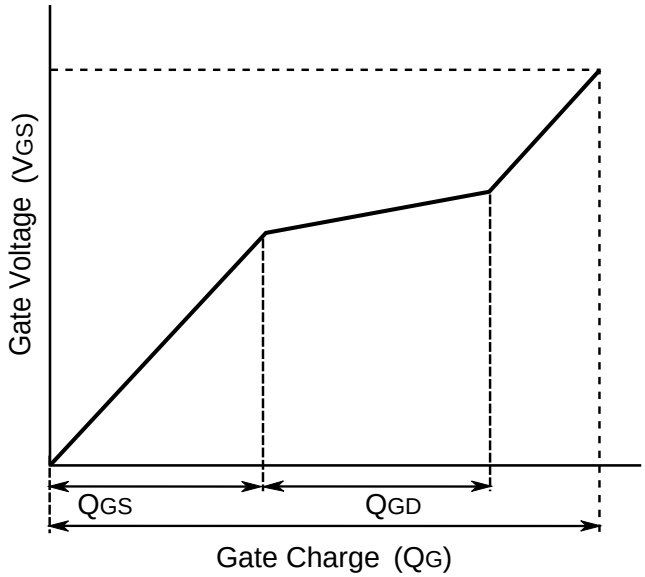


T_j = 25°C; V_{GS} = -5/+15V; I_{DS} = 35 A

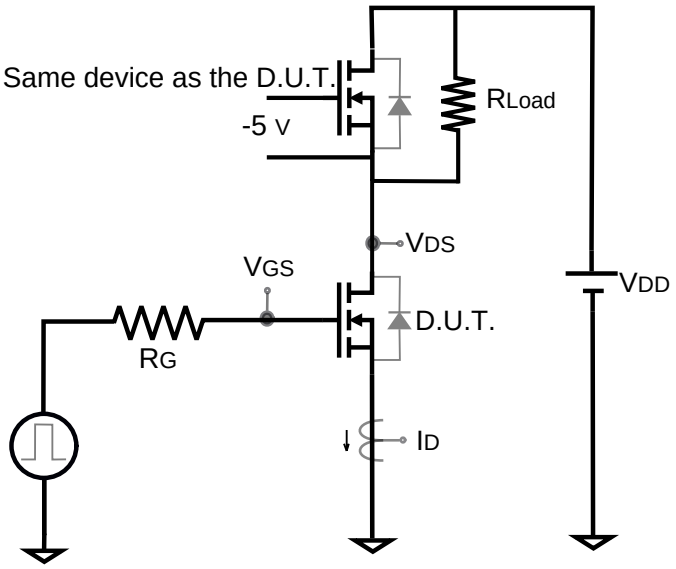
Gate Charge Circuit



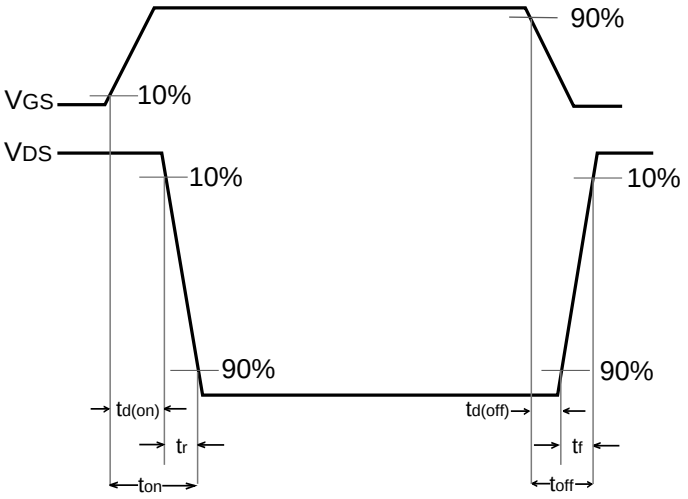
Gate Charge Waveform



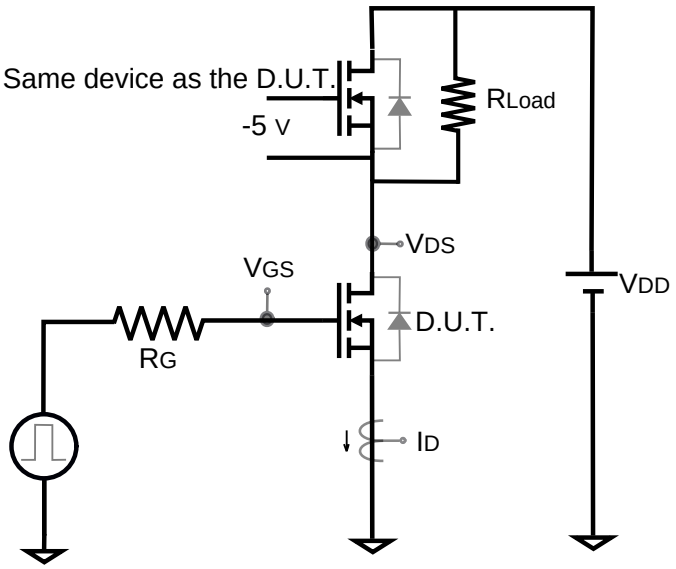
Switching Time Circuit



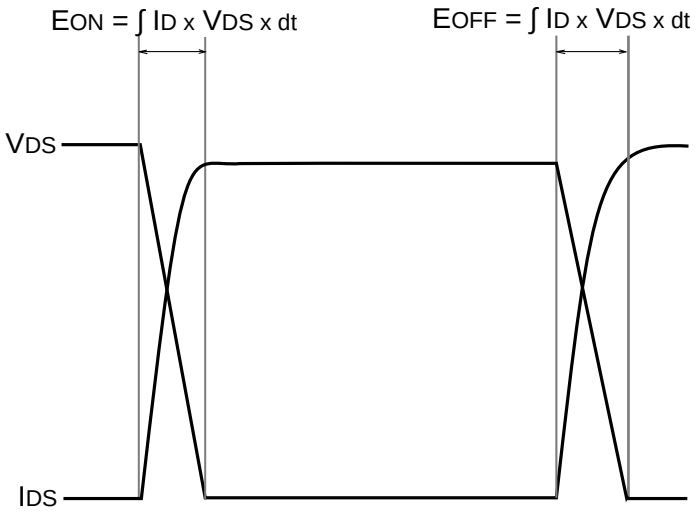
Switching Time Waveform



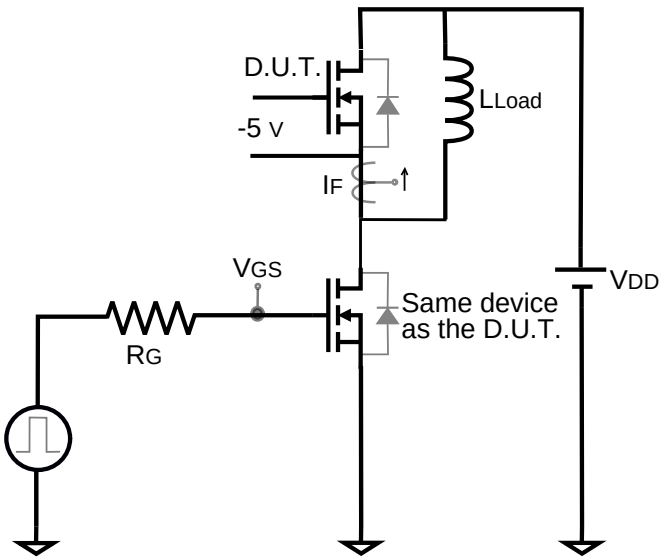
Switching Energy Circuit



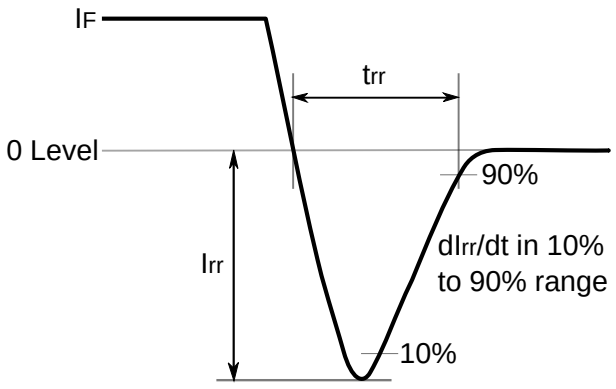
Switching Energy Waveform



Reverse Recovery Circuit



Reverse Recovery Waveform



Mechanical Parameters

This information is confidential, please contact **sales@genesicsemi.com** to learn more.

Chip Dimensions

This information is confidential, please contact **sales@genesicsemi.com** to learn more.

NOTE

1. CONTROLLED DIMENSION IS MILLIMETER.
2. DIMENSIONS DO NOT INCLUDE END FLASH, MOLD FLASH, MATERIAL PROTRUSIONS.

Compliance

RoHS Compliance

The levels of RoHS restricted materials in this product are below the maximum concentration values (also referred to as the threshold limits) permitted for such substances, or are used in an exempted application, in accordance with EU Directive 2011/65/EC (RoHS 2), as adopted by EU member states on January 2, 2013 and amended on March 31, 2015 by EU Directive 2015/863. RoHS Declarations for this product can be obtained from your GeneSiC representative.

REACH Compliance

REACH substances of high concern (SVHCs) information is available for this product. Since the European Chemical Agency (ECHA) has published notice of their intent to frequently revise the SVHC listing for the foreseeable future, please contact a GeneSiC representative to insure you get the most up-to-date REACH SVHC Declaration. REACH banned substance information (REACH Article 67) is also available upon request.

Disclaimer

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Unless otherwise expressly indicated, GeneSiC products are not designed, tested or authorized for use in life-saving, medical, aircraft navigation, communication, air traffic control and weapons systems, nor in applications where their failure may result in death, personal injury and/or property damage.

Related Links

- SPICE Models: https://www.genesicsemi.com/sic-mosfet/G3R40MT12-CAL/G3R40MT12-CAL_SPICE.zip
- PLECS Models: https://www.genesicsemi.com/sic-mosfet/G3R40MT12-CAL/G3R40MT12-CAL_PLECS.zip
- CAD Models: https://www.genesicsemi.com/sic-mosfet/G3R40MT12-CAL/G3R40MT12-CAL_3D.zip
- Gate Driver Reference: https://www.genesicsemi.com/technical-support
- Evaluation Boards: https://www.genesicsemi.com/technical-support
- Reliability: https://www.genesicsemi.com/reliability
- Compliance: https://www.genesicsemi.com/compliance
- Quality Manual: https://www.genesicsemi.com/quality

Revision History

- Rev 21/Jan: Added switching time and switching energy data
- Supersedes: Rev 20/Jun, Rev 20/Aug

www.genesicsemi.com/sic-mosfet/

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